



Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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Complete if Known

Application Number	10/602,315
Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2829
Examiner Name	Sarkar, Asok

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Attorney Docket No: 1303.107US1

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td colspan="2" style="font-size: small;">Complete if Known</td> </tr> <tr> <td style="width: 60%;">Application Number</td> <td>10/602,315</td> </tr> <tr> <td>Filing Date</td> <td>June 24, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>2829</td> </tr> <tr> <td>Examiner Name</td> <td>Sarkar, Asok</td> </tr> </table>	Complete if Known		Application Number	10/602,315	Filing Date	June 24, 2003	First Named Inventor	Ahn, Kie	Group Art Unit	2829	Examiner Name	Sarkar, Asok
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Substitute Disclosure Statement Form (PTO-1449)

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